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DIELECTRIC MEASUREMENT PROBE FOR CURVED SURFACES

STATEMENT OF GOVERNMENT INTEREST

[0001] The present application claims the benefit of United States Provisional Application Serial Number 62/589,621 filed on 22 November 2017 by the inventor, David F. Rivera and entitled "Dielectric Measurement Probe for Curved Surfaces".

[0002] The invention described herein may be manufactured and used by or for the Government of the United States of America for governmental purposes without the payment of any royalties thereon or therefor.

CROSS REFERENCE TO RELATED PATENT APPLICATIONS

[0003] None.

BACKGROUND OF THE INVENTION

1) Field of the Invention

[0004] The present invention is a device and supporting assembly for measuring electrical properties over a range of frequencies for a dielectric material in which surface contours of the material are concave or convex.

2) Description of the Prior Art

[0005] The nondestructive measurement of insulating materials includes using an open-ended coaxial probe. The coaxial probe is unique among techniques for measuring the dielectric properties of materials. Because the open-ended coaxial probe uses a non-invasive method that only requires contact with a material sample; the probe can characterize properties over a broad range of frequencies.

[0006] In Rivera (United States Patent No. 7,495,454), a coaxial probe comprises two components. One component is a section of open coaxial line attached to a conducting flange. When placed firmly against the dielectric material of an insulator; the probe determines a relative permittivity as a function of frequency from measurements that includes a complex reflection coefficient.

[0007] The open-ended coaxial probe relies on a testing surface in which the surface is relatively flat and smooth. When the probe is placed on a surface which is not flat; errors result because of air gaps between the aperture surface and the sample. To accurately account for the presence of air gaps, computer modeling methods are required to fully represent the electromagnetic fields within the material and in the air gap region.

[0008] Examples exist for measuring the dielectric properties of a curved dielectric surface. In a prior art device, a center conductor of a probe extends to contact the material and minimize the air gap. A finite-element method is used; thereby, requiring the probe and dielectric surface to be accurately modeled. This is disadvantageous because coaxial probes are non-standard devices which could have any size; thereby, requiring a time-consuming effort for modeling varying sizes and shapes.

[0009] As such, a need exists for a probe which can contact varying surfaces such as a convex or concave dielectric surface without air gaps.

SUMMARY OF THE INVENTION

[0010] It is therefore a primary object and general purpose of the present invention to provide a probe and a calibration saddle for the probe to contact varying surfaces of a material including concave or convex dielectric surfaces in order to provide non-destructive measurement of the complex relative dielectric permittivity of the material.

[0011] To attain the present invention, a measurement probe and a calibration saddle is disclosed for the non-destructive measurement of complex relative dielectric permittivity of a

dielectric material in which the material can have varying shapes.

[0012] The probe generally comprises a center electrode, two side electrodes and a mounting harness. The mounting harness serves as a central support with the side electrodes and a feed point connector attached to the harness. The center electrode is soldered to the feed point connector. Apertures in the mounting harness allow attachment of the probe to a mechanically adjustable arm in order to guide the probe onto a dielectric sample.

[0013] A bulbous tip of the center electrode is used to contact a dielectric material under test. The bulbous tip includes a surface area for improved measurement sensitivity and a smooth contour to permit rotation on the dielectric material without marring the material. The probe can rest perpendicularly on a dielectric material as well as operate in a tilted position without a loss of measurement accuracy.

[0014] The calibration saddle ensures that measurements of the reflection coefficient using the probe, are conducted near the bulbous tip. When the probe inserted into the saddle; the center electrode and the side electrodes short together with a clear indication on a vector network analyzer to which the probe is attached. By adjusting an electrical delay on the analyzer, a reference plane shifts from the end of a coaxial transmission

line connected to the feed point connector to the bulbous tip.

[0015] The voltage wave generated by a vector network analyzer is guided between the electrodes, toward the bulbous tip and into the dielectric material. Gap spacing between the center electrode and the side electrodes determines the depth of the electric field infringing into the dielectric material within the saddle. The material under test reflects the incoming voltage wave back to the network analyzer with the ratio of the reflected and forward voltages forming a reflection coefficient. The dielectric properties of the material are calculated using the reflection coefficient data.

[0016] The effective permittivity detected by the probe depends on the radius of the probe tip, the radius of the insulator material and the true permittivity of the material. When the bulbous tip rests on a curved dielectric; the electric field of the probe retains the same shape with a dielectric material regardless whether the material is convex or concave.

[0017] The probe can be used in the manufacture and quality control of antenna radomes of circular and semi-circular shape. The probe can also be used to measure the moisture content of building materials such as lumber and cast concrete as well as measuring the dielectric properties of soil and rocks, biological materials or agricultural products.

BRIEF DESCRIPTION OF THE DRAWINGS

[0018] A more complete understanding of the invention and many of the attendant advantages thereto will be readily appreciated as the same becomes better understood by reference to the following detailed description when considered in conjunction with the accompanying drawings wherein like reference numerals and symbols designate identical or corresponding parts throughout the several views and wherein:

[0019] **FIG. 1** depicts an isometric view of a dielectric measurement probe of the present invention;

[0020] **FIG. 2** depicts an alternate isometric view of the dielectric measurement probe of the present invention with the view taken along the reference lines **2-2** of **FIG. 1**;

[0021] **FIG. 3** depicts an isometric view of the dielectric measurement probe of the present invention with a cover plate and dielectric support positioned on the measurement probe;

[0022] **FIG. 4** depicts an isometric view of the dielectric measurement probe of the present invention with a cover plate, dielectric support, and fasteners installed on the measurement probe;

[0023] **FIG. 5** depicts the probe of the present application resting on a dielectric material under test;

[0024] **FIG. 6** depicts the probe of the present application resting at an angle on the dielectric material under test;

[0025] FIG. 7 depicts an isometric view of a calibration saddle for the probe of the present invention;

[0026] FIG. 8 depicts an electrical circuit of the probe of the present invention; and

[0027] FIG. 9 depicts flow chart for the use of the probe of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

[0028] The invention is a probe 10 for non-destructive measurement of complex relative dielectric permittivity ϵ_m of an material in which the material can have varying shapes. The complex relative permittivity is determined by Equation (1) as:

$$\epsilon_m = \epsilon'_m - j\epsilon''_m \quad (1)$$

where ϵ'_m is the dielectric constant and ϵ''_m is the loss factor and $j = \sqrt{-1}$.

[0029] A loss tangent $\tan\delta$ is defined by Equation (2) as

$$\tan\delta = \frac{\epsilon''_m}{\epsilon'_m} \quad (2)$$

where the dielectric permittivity is determined with a complex reflection coefficient.

[0030] In FIG. 1 and FIG. 2, the probe 10 comprises a center electrode 12, two side electrodes 14 and a mounting harness 16. The mounting harness 16 serves as a central support because the side electrodes 14 (labeled SE1 and SE2 on the figure) and a

feed point connector **18** are attached to the mounting harness. As shown in **FIG. 3** and **FIG. 4**, the center electrode **12** is soldered to the feed point connector **18** and is protected by a cover plate **20**. The cover plate **20** is attached by fasteners **22**.

[0031] The side electrodes **14** and the mounting harness **16** are preferably made from stainless steel for corrosion resistance but can be made from other non-ferrous materials. A dielectric cover plate **24** is preferably made from Delrin but can be made from other high-strength polymeric composites such as flame-retardant electrical grade fiberglass.

[0032] Apertures **26** or holes in the mounting harness **16** allow attachment to a mechanically adjustable arm (not shown) to guide the probe **10** onto a dielectric sample. This feature frees an operator from having to press the probe **10** firmly against the sample for a sustained period of time; thereby, reducing fatigue and attendant errors in measurement.

[0033] A bulbous tip **28** of the center electrode **12** is used to contact a dielectric material **200** under test. The bulbous tip **28** includes a large surface area for improved measurement sensitivity and a smooth contour to permit rotation on the dielectric material without marring the finish of the material.

[0034] As shown in **FIG. 5** and **FIG. 6**, the probe **10** can rest perpendicularly on the dielectric material **200** as well as operate in a tilted position from the perpendicular without a

loss of measurement accuracy. The bulbous tip **28** can pivot on an axle between the side electrodes **14** to achieve the tilted position. The maximum deviation angle from the perpendicular is approximately $\pm 20^\circ$. This feature permits some operator error in positioning the probe **10** on the dielectric material **200** while still obtaining accurate measurements.

[0035] Ideally, the probe **10** is positioned perpendicularly over the dielectric material **200** but there may be circumstances when the probe cannot be positioned in this manner. In these circumstances, the probe **10** can be tilted to an angle (symbol: ϕ) over the surface of the dielectric material **200** and can still yield reliable results.

[0036] In **FIG. 7**, a calibration saddle **100** for the probe **10** is shown. The calibration saddle **100** ensures that measurements of the reflection coefficient (Γ) of the dielectric material **200** are referred to a region near the bulbous tip **28** of the probe **10**. In use, the probe would be inserted in direction "A" into a recess area **102** of the calibration saddle **100**. The probe **10** is then inserted in direction "A" with the result that the center electrode **12** and the side electrodes **14** short together, with a clear indication on a vector network analyzer to which the probe is attached. By adjusting an electrical delay on the vector

network analyzer, a reference plane is shifted from the end of a coaxial transmission line connected to the feed point connector **18** of the probe **10** to a region of the bulbous tip **28**.

[0037] As shown in the figures, the probe **10** has multiple parts. The shapes of the various parts provide a unified device that can withstand repeated handling. Important characteristics of the probe **10** are the gap spacing between the center electrode **12**, the side electrodes **14** and the radius of the bulbous tip **28**. The metal parts of the probe **10** can be fabricated with corrosion resistant metal such as stainless steel, naval brass or phosphor bronze.

[0038] The gap spacing between the center electrode **12** and the side electrodes **14** determines the depth of the electric field infringing into the dielectric material **200**. The radius of the bulbous tip **28** increases the sensitivity of the probe **10** when measuring the permittivity of materials having air voids.

[0039] The physical size of the probe **10** is small compared to the smallest operating wavelength. This permits a simple equivalent circuit representation. The operating wavelength (λ) is defined by Equation (3)

$$\lambda = \frac{v_0}{f} \tag{3}$$

where v_0 is the speed of light and f is the operating frequency.

[0040] The probe **10**, as illustrated in **FIG. 1**, is limited in operation to approximately 800 MHz where the wavelength (λ) is 15

inches. With the overall size of the probe **10** being (in inches) 5.75 wide x 5.875 tall x 1.5 thick; the corresponding electrical size of the probe is 0.39λ wide x 0.40λ tall x 0.10λ thick. The corresponding equivalent circuit is shown in **FIG. 8**.

[0041] In the circuit of **FIG. 8**, the bulbous tip **28** is represented by a parallel-connected capacitance C_0 (units: Farads, F) and conductance G (units: Siemens, S) that extends outward from the probe **10**, which is represented as a transmission line conduit with a characteristic (wave) impedance Z_0 and with a length equal to the probe height H . The parallel-connected capacitance C_0 and conductance G form an admittance ($Y(\omega)$, units: Siemens, S) which is calculated by Equation **(4)**

$$Y(\omega) = G + j\omega C_0 \quad (4)$$

where ω is the angular frequency (radians per second, rad/s), being proportional to the operating frequency f by Equation **(5)**

$$\omega = 2\pi f. \quad (5)$$

[0042] The significance of the electrical quantities describing the probe **10** are that the characteristic impedance Z_0 is the resistance experienced by a propagating electromagnetic wave as the wave travels from the feed point connector **18** to the bulbous tip **28**. The electrical quantities include: a capacitance C_0 representing a stored electric field energy at the bulbous tip **28**; a conductance G representing energy loss from

the bulbous tip in the form of radiation; and a phase constant β describing how a sinusoidal wave changes in amplitude as the wave travels between two points.

[0043] The phase constant β of the probe **10** (units: radians per meter, rad/m) is calculated by Equation **(6)**

$$\beta \approx 2\pi\sqrt{\epsilon_s^*}/\lambda \quad (6)$$

where λ is previously defined and ϵ_s^* is an effective (or apparent) value of the dielectric constant of the insulating support that holds the conducting electrodes together ($\epsilon_s^* \approx 1.89$). The product (βH) of the phase constant β and the probe height H is the phase angle (units: radians) and describes a fraction of a full cycle of an electromagnetic wave arriving at the probe **10**.

[0044] The value of C_0 and Z_0 have been measured to 0.30 picofarads (pF) and 43.7 ohms, respectively. Since the electrode spacing (s) is electrically small (the ratio $s/\lambda \ll 1$), the conductance G depends on the height of the probe (H) and the operating wavelength (λ) as expressed by Equation **(7)**

$$G \approx m \left(\frac{H}{\lambda}\right)^n \quad (7)$$

where the constant (m) and exponent (n) are experimentally determined.

[0045] In the operational frequency range, the height-to-wavelength ratio (H/λ) of the probe **10** is very small compared to the product ωC_0 (known as the susceptance, symbol: B , units: Siemens, S) or by Equation (8)

$$G \ll \omega C_0. \quad (8)$$

[0046] The critical quantity is the capacitance C_0 of the bulbous tip **28** which should be as large as practicable as the capacitance depends on the surface area of the bulbous tip.

[0047] When the bulbous tip **28** contacts the dielectric material **200**, the value of capacitance C_0 of the tip proportionally with the permittivity ϵ_m , of the material forms a modified admittance $Y^*(\omega)$ by Equation (9)

$$Y^*(\omega) \approx j\omega\epsilon_m^e C_0 \quad (9)$$

where ϵ_m^e is an apparent value of the permittivity. This apparent permittivity is smaller than the true value (ϵ_m) because of a radius of curvature of the dielectric material **200**.

[0048] A voltage wave traveling down an equivalent transmission line encounters this modified admittance and reflects a wave back whose strength is proportional to the modified admittance, from which the permittivity of the dielectric material **200** is inferred.

[0049] In the operation of the probe **10**, a voltage wave generated by a vector network analyzer (not shown) is guided

between the electrodes **14** and travels toward the bulbous tip **28** and into the dielectric material **200**. The dielectric material **200** reflects this incoming voltage wave back to the network analyzer with an amplitude and phase that is unique to that material. The ratio of the reflected and forward voltages forms the reflection coefficient (symbol: Γ). The dielectric properties of the dielectric material **200** are inferred from reflection coefficient data.

[0050] The reflection coefficient is a complex quantity and may be written by Equation **(10)**

$$\Gamma = \Gamma' - j\Gamma'' \quad (10)$$

but is commonly represented by the complex exponential quantity of Equation **(11)**

$$\Gamma = Me^{-j\theta} \quad (11)$$

where M is the magnitude, defined in Equation **(12)** as

$$M = \sqrt{(\Gamma')^2 + (\Gamma'')^2} \quad (12)$$

and θ is the phase angle defined in Equation **(13)** as

$$\theta = \tan^{-1}\left(\frac{\Gamma''}{\Gamma'}\right). \quad (13)$$

[0051] The probe **10** demonstrates that for low loss materials (when $\tan\delta \leq 0.05$), the reflection coefficient phase angle θ changes more than the magnitude M . Lossy materials ($\tan\delta > 0.05$) undergo marked changes in both M and θ .

[0052] Attendant with the voltage wave propagating between the electrodes **14**; the energized probe **10** will also have an electric current flowing over the surface of the probe. The flow paths taken by the current with amplitude changes over the surface of the probe **10**; generate an electromagnetic emission that is characteristic of numerous vector electric and magnetic field components.

[0053] With the probe **10** energized, small electric and magnetic field sensors (in the form of thin-wire dipoles and loop antennas), pass over the probe surface **200** at a close range to determine the vector character of emitted fields. Close range is defined as the radial distance (symbol: ρ) between the probe **10** and the field sensors, with the distance being very small compared to the operating wavelength (λ) as shown in Equation (14)

$$\frac{\rho}{\lambda} \ll 1. \tag{14}$$

[0054] When the probe **10** rests on a material; the emitted electric field is divided over a portion in the air space above the material and a portion in the dielectric material **200**. The magnetic field emitted by the probe **10** can propagate without attenuation through the dielectric material **200**.

[0055] Experiments performed with the probe **10** indicate that the depth of electric field penetration (d_e) into a dielectric

material **200** is directly proportional to the electrode spacing (s) and is expressed in Equation **(15)** as

$$d_e \approx 4s. \tag{15}$$

[0056] The probe **10** in **FIG. 1** can penetrate into a material to a depth of approximately one inch. The depth is determined by measurements of the phase (θ) of the reflection coefficient, which is more sensitive to changes in material thickness than the reflection coefficient magnitude (M). The material thickness (t) is normalized by an electrode spacing of the probe **10**.

[0057] For $t/s \geq 4$, a phase change is within 95% of the terminal phase value obtained with an infinitely thick dielectric. In practice, the dielectric material **200** does not need to be excessively thick in order to obtain an accurate determination of permittivity.

[0058] When the field penetration depth is such that the dielectric material **200** appears as if infinitely thick (that is, when $d_e \approx 4s$); the field occupies an irregularly-shaped volume V_s that may be represented as geometric proportions of the probe **10**, expressed in Equation **(16)** as

$$V_s \approx (k_1s + k_2W_1 + k_3W_2)as \tag{16}$$

where k_1 , k_2 and k_3 are frequency and material dependent constants. W_1 and W_2 are the widths of the center electrode **12**

and the side electrodes **14** with a and s respectively being a radius of the bulbous tip **28** and electrode spacing. The probe **10** can detect anomalous defects in dielectrics over a region having the sensing volume V_s .

[0059] The determination of the true (or bulk) permittivity ϵ_m of a curved insulator is complicated by the fact that the electric field(s) emitted by the probe **10** is (are) unequally split between the air and material regions. Also, the non-symmetrical geometric shape of the probe **10** generates a complicated electromagnetic field emission characteristic which does not permit a simple analytic implementation.

[0060] An infinite series formula is derived by the following observations: in which in the air region, the electric lines are roughly parallel to the dielectric boundary; in the immediate vicinity of the air-dielectric boundary, part of the electric field lines are parallel and parts are perpendicular; and in the dielectric, the field lines are roughly perpendicular.

[0061] As the radius of the dielectric material **200** decreases relative to the radius of the bulbous tip **28**; the field intensity in the air region increases and the probe **10** detects an effective permittivity with a value between the value obtained for air ($\epsilon_m = 1$) and the bulk permittivity of the material. As such, the effective permittivity ϵ_m^e detected by the

probe **10** depends on: the radius (symbol: a) of the bulbous tip **28**; the radius (symbol: b) of the dielectric material **200**; and the true (ϵ_m) permittivity of the material.

[0062] Since the dimensions of the probe **10** and the dielectric material **200** are assumed to be small compared to the smallest operating wavelength, frequency-dependent effects on the effective permittivity ϵ_m^e are assumed to be due to innate changes in true permittivity ϵ_m with frequency. Examples include: when $b/a \rightarrow \infty$ (a flat surface), $\epsilon_m^e = \epsilon_m$; when $b/a \rightarrow 0$ (a vanishing cylinder), $\epsilon_m^e = 1$; when $\epsilon_m = 1$ and b/a is arbitrary, $\epsilon_m^e = 1$; and the rate-of-decrease in ϵ_m^e as $b/a \rightarrow 0$ is dependent on ϵ_m .

[0063] Observations indicate that a formula for ϵ_m^e should have at least two terms. A first term represents the absence of a dielectric at the bulbous tip **28** (that is, $\epsilon_m^e = 1$ when $\epsilon_m = 1$) and a second term that accounts for the presence of a dielectric material **200** that curves away or toward the tip. The previous considerations permit deduction of the formula in the form of an infinite series, as represented in Equation **(17)**:

$$\epsilon_m^e = 1 + \left[\frac{(\epsilon_m - 1)F(\epsilon_m, a, b)}{1 + F(\epsilon_m, a, b)} \right] \quad (17)$$

whereas in Equation **(18)**:

F is a function of ϵ_m, a, b having a mathematical form as:

$$F(\epsilon_m, a, b) = \sum_{i=-\infty}^{\infty} \sum_{j=-\infty}^{\infty} c_{ij}(\epsilon_m)^i \left(\frac{b}{a}\right)^j \quad (18)$$

and c_{ij} are unknown coefficients.

[0064] The infinite series formula for ϵ_m^e describes a spatial orientation of the electric field lines emitted by the probe **10** when in contact with a curved dielectric material. It is assumed that the probe **10** can be distorted such that the electric field emitted into the dielectric sample travels in a straight line between two points, in a manner similar to a parallel-plate capacitor. The electric field lines in the parallel-plate capacitor would span a gap.

[0065] When the bulbous tip **28** rests on a curved dielectric; the electric field of the probe **10** retains the same shape (with curved lines) with a dielectric material **200** regardless whether the material is convex or concave. The infinite series formula expresses an electromagnetic field equivalence between the probe **10** resting on a curved dielectric emitting a curved electric field, and a parallel-plate capacitor with a linear electric field and two curved dielectric boundaries (air and dielectric).

[0066] The proportions of these dielectrics is dependent on the ratio of the radii of the bulbous tip **28** and dielectric sample (b/a) as well as the permittivity of the dielectric (ϵ_m). Given the asymmetric shape of the probe **10** and the

electromagnetic field interaction between the probe and the dielectric material **200**; the empirical infinite-series formula is a reasonable representation of the physics of the probe.

[0067] The determination of the permittivity of a material with a finite thickness requires additional observations to determine a solution. An infinitely thick material has a physical thickness (t) that is equal to (or greater than) four times the electrode spacing (s), or as in Equation **(19)**

$$t \geq 4s. \tag{19}$$

[0068] Under this condition, any additional increase in the material thickness results in an incremental (and negligible) change in the phase angle (θ) of the reflection coefficient. Alternatively, thin material is one in which the inequality, as shown in Equation **(20)** applies

$$t < 4s. \tag{20}$$

[0069] Under this condition, the reflection coefficient (as measured at the feed point connector **18**) changes with thickness because the field emitted by the probe **10** penetrates through the thin material under test and continues to a depth defined by Equation **(21)** where the material attains a negligibly small amplitude

$$d \approx 4s. \tag{21}$$

[0070] If the infinite-series formula is used to determine the permittivity ϵ_m ; the formula would yield an erroneous answer because the probe **10** detects a smaller value of ϵ_m^e due to an interaction between the thin material and the air space below.

[0071] Returning to the parallel-plate equivalent, two materials would appear as series-connected capacitors with unequal amounts of dielectrics. To solve this problem, the layered dielectrics are replaced with a homogeneous dielectric having an effective permittivity value ϵ^* that is expressed in terms of the constituent dielectrics ($\epsilon_{m1}, \epsilon_{m2}$) and the thickness t . With the effective permittivity of the two-layer dielectric determined, this value is used to calculate the overall dielectric value seen by the probe **10**. The infinite series formula is modified and written to be defined by Equation (22)

$$(\epsilon_m^e)^* = 1 + \left[\frac{(\epsilon^* - 1)F(\epsilon^*, a, b)}{1 + F(\epsilon^*, a, b)} \right] \quad (22)$$

where

$$F(\epsilon^*, a, b) = \sum_{i=-\infty}^{\infty} \sum_{j=-\infty}^{\infty} c_{ij} (\epsilon^*)^i \left(\frac{b}{a}\right)^j. \quad (23)$$

[0072] The effective permittivity ϵ^* of the layered dielectrics can be defined by Equation (24)

$$\epsilon^* \approx \frac{\alpha + t^\beta}{\left[\left(\frac{t^\beta}{\epsilon_{m1}}\right) + \left(\frac{\alpha}{\epsilon_{m2}}\right) \right]} \quad (24)$$

where α is a shape-dependent numerical constant for the probe **10**, and β is an exponent (not to be confused with phase constant).

[0073] The formula, described above, simplifies measuring a thin material under test backed by air. If $\epsilon_{m1} = \epsilon_m$ (the bulk relative permittivity of the material under test) and $\epsilon_{m2} = 1$ (the dielectric material under test backed by air), the effective permittivity formula reduces to be defined by Equation **(25)**

$$\epsilon^* \approx \frac{\epsilon_m}{\left\{ 1 + \left[\frac{\epsilon_m^{-1}}{1 + (t^\beta/\alpha)} \right] \right\}} \quad (25)$$

[0074] Experiments with numerous convex dielectrics indicate that the exponent β is between 1.4 and 1.6, suggesting a mean value of $\beta \approx 1.5$. The probe constant α is $\alpha \approx 0.06$. For concave materials, the expression for ϵ^* will also be the same form because of similar electric field line orientations within the thin layer, but with differing constants α and β .

[0075] A probe **10** can behave as a transmission line because electrode spacing is a small fraction of a wavelength at the highest frequency of operation. Capacitance C_a is the ratio of the per-unit-length electric charge and voltage ($C = Q/V$) between adjacent electrodes (ground and center, respectively) in an air space above a dielectric material. A fringing capacitance C_o of the bulbous tip **28** is the component that interacts with the

dielectric material **200**. The total capacitance $C_t(\epsilon)$ seen at the bulbous tip **28** is the sum in Equation **(26)** as

$$C_t(\epsilon) = C_a + C_o(\epsilon - 1). \quad (26)$$

[0076] The formula above indicates that when the dielectric is air ($\epsilon = 1$), $C_t(1) = C_a$. Let C_m be the total capacitance at the bulbous tip **28** with the material under test as defined by Equation **(27)**

$$C_m = C_t(\epsilon_m) = C_{air} + (\epsilon_m - 1)C_o. \quad (27)$$

[0077] Let C_s be the total capacitance at the bulbous tip **28** with a dielectric having a permittivity ϵ_s calculated by Equation **(28)**

$$C_s = C_t(\epsilon_s) = C_{air} + (\epsilon_s - 1)C_o. \quad (28)$$

[0078] Using the capacitances C_m and C_s , solve for ϵ_m by eliminating C_o and obtain from Equation **(29)**

$$\epsilon_m = 1 + (\epsilon_s - 1) \left(\frac{C_m - C_{air}}{C_s - C_{air}} \right). \quad (29)$$

[0079] If each capacitance is written in terms of impedance Z , defined by Equation **(30)**

$$Z = \frac{1}{j\omega C} \quad (30)$$

then

$$\epsilon_m = 1 + (\epsilon_s - 1) \left(\frac{Z_s}{Z_m} \right) \left(\frac{Z_m - Z_{air}}{Z_s - Z_{air}} \right). \quad (31)$$

[0080] The formula, previously described, indicates that the permittivity of the unknown material is determined solely by measuring the impedance of the material under test, air, and a

known dielectric standard at the bulbous tip **28**. A way to circumvent Equation **(31)** is to mathematically translate these impedances to the feed point connector or input port **18**. This will involve a measurement of a short circuit.

[0081] Let Z_{oc}^p be the impedance at the input port **18** with an open circuit at the bulbous tip **28**. Also, let Z_{sc}^p be the impedance at input port **18** with an short circuit at the bulbous tip **28**. Let Z_s^p be the impedance at input port **18** with a dielectric standard at the bulbous tip **28** and let Z_m^p be the impedance at the input port with the dielectric material **200** at the bulbous tip.

[0082] The impedances Z_s , Z_m and Z_{air} can be rewritten in terms of the quantities above by Equation **(32)** and Equation **(33)**

$$Z_s = Z_{oc}^p \left(\frac{Z_{sc}^p - Z_s^p}{Z_s^p - Z_{oc}^p} \right) \quad (32)$$

$$Z_m = Z_{oc}^p \left(\frac{Z_{sc}^p - Z_m^p}{Z_m^p - Z_{oc}^p} \right) \quad (33)$$

and as Equation **(34)**

$$Z_{air} = Z_{oc}^p. \quad (34)$$

[0083] The substitution of these quantities in the ϵ_m formula results in Equation **(35)**

$$\epsilon_m^e = 1 + (\epsilon_s - 1) \left(\frac{Z_{sc}^p - Z_s^p}{Z_{oc}^p - Z_s^p} \right) \left(\frac{Z_{oc}^p - Z_m^p}{Z_{sc}^p - Z_m^p} \right) \quad (35)$$

where the superscript p is at the input port. Since a vector network analyzer measures complex reflection coefficients (Γ); a

formula for the relative permittivity of the dielectric material **200** in terms of Γ would be more useful.

[0084] The final step in the derivation requires writing each impedance Z in terms of the respective reflection coefficients using the standard definition of Equation **(36)**

$$Z = Z_o \left(\frac{1+\Gamma}{1-\Gamma} \right) \quad (36)$$

where Z_o is a measurement reference or system impedance (typically 50 ohms). The substitution of the formula above into the expression for ϵ_m^e becomes

$$\epsilon_m^e = 1 + (\epsilon_s - 1) \left(\frac{\Gamma_{sc} - \Gamma_s}{\Gamma_{oc} - \Gamma_s} \right) \left(\frac{\Gamma_{oc} - \Gamma_m}{\Gamma_{sc} - \Gamma_m} \right) \quad (37)$$

where in Equation **(37)**, superscript p is suppressed.

[0085] Although the method for the relative permittivity ϵ_m is derived for a flat dielectric, the method also works for curved dielectrics. If the ratio is $b/a > 4$, the dielectric material **200** can be considered to be flat and the above formula for ϵ_m^e can be used. If the ratio is $b/a \leq 4$, cylindrical standards (concave or convex) must be used for calibration with the same formula for the flat dielectric case, but renaming $(\epsilon_m^e)^*$ in order to distinguish between the two cases, so in Equation **(38)**

$$(\epsilon_m^e)^* = 1 + (\epsilon_s^c - 1) \left[\frac{\Gamma_{sc}^c - \Gamma_s^c}{\Gamma_{oc}^c - \Gamma_s^c} \right] \left[\frac{\Gamma_{oc} - \Gamma_m^c}{\Gamma_{sc}^c - \Gamma_m^c} \right] \quad (38)$$

where $(\epsilon_m^e)^*$ is the permittivity of the unknown curved material **200**; ϵ_s^c is the permittivity of a known curved dielectric standard;

Γ_{oc} is the complex reflection coefficient of the probe **10**, measured at the feed point connector **18** with the bulbous tip **28** terminated by air (the subscript *oc* meaning an open circuit); Γ_{sc}^c is the complex reflection coefficient of the probe, measured at the feed point connector, with the probe tip touching a curved metal surface (the subscript *sc* meaning a short circuit); Γ_s^c is the complex reflection coefficient of the probe, measured at the feed point connector, with the bulbous tip touching the surface of a curved dielectric with a known value (the subscript *s* meaning a dielectric standard) and Γ_m^c is the complex reflection coefficient of the probe, measured at the connector port, with the bulbous tip touching the surface of the curved material (the subscript *m* meaning the material under test or the dielectric material **200**).

[0086] In the range of $b/a \leq 4$, low-loss cylindrical standards are required for calibration. Ideally, a large collection of cylindrical sizes could be available to closely match the material under test in order to accurately measure the dielectric properties.

[0087] Low-loss cylinders of varying radii (*b*) having a fixed permittivity ϵ_s and a probe tip radius (*a*) indicate that the magnitude of the reflection coefficient *M* has a rate-of-change (or slope) of *M* with radius *b* written in Equation **(39)** as

$$\frac{\Delta M}{\Delta b} = p_1(a, \epsilon_s). \quad (39)$$

[0088] Similarly, the rate-of-change of the reflection coefficient phase angle θ with a cylindrical radius b written in Equation (40) as

$$\frac{\Delta \theta}{\Delta b} = p_2(a, \epsilon_s) \cdot f \quad (40)$$

where f is the frequency and $p_1(a, \epsilon_s)$ and $p_2(a, \epsilon_s)$ are constants that depend on the radius a of the bulbous tip **28** and the permittivity of the standard, ϵ_s .

[0089] For cylinders made from G-10/FR-4 fiberglass with $\epsilon_s = 4.7 - j 0.08$ and a probe tip radius $a = 0.75$ inch, these constants have the values $p_1(a, \epsilon_s) \approx 0.002$ and $p_2(a, \epsilon_s) \approx - 0.026$ over the frequency (f) range of 50 to 400 MHz. The units of p_1 and p_2 are per inch (inch^{-1}) and degree per inch per MHz ($\text{deg} \cdot \text{inch}^{-1} \cdot \text{MHz}^{-1}$), respectively.

[0090] The rate-of-change of the reflection coefficient magnitude M with a metal cylinder of radius b has the form written in Equation (41) as

$$\frac{\Delta M}{\Delta b} = \frac{p_3(a, \sigma)}{f} \quad (41)$$

and that the rate-of-change of the reflection coefficient phase angle θ written in Equation (42) as

$$\frac{\Delta\theta}{\Delta b} = \frac{p_4(a,\sigma) \cdot f}{b} \quad (42)$$

where the constants p_3 and p_4 depend on the radius a and electrical conductivity σ of the metal cylinder.

[0091] The values of these constants for aluminum cylinders ($\sigma = 3.5 \times 10^7$ Siemens per meter, S/m) are $p_3(a,\sigma) \approx -0.00003$ and $p_4(a,\sigma) \approx -0.055$. The units of the constants p_3 and p_4 are MHz per inch ($\text{MHz} \cdot \text{inch}^{-1}$) and degrees per MHz ($\text{deg} \cdot \text{MHz}^{-1}$), respectively, over the frequency range of 200 MHz to 600 MHz.

[0092] The results above suggest that the rate-of-change in the reflection coefficient (magnitude and phase) are sufficiently small such that diameters of the cylindrical dielectric and short circuit standards do not have to be exact in size with the material under test; some deviation is permissible. For a given radius of a material under test, the maximum deviation in the radius of the cylindrical dielectric standard and short circuit should be within $\pm 25\%$ to yield reliable permittivity measurement results.

[0093] Generally speaking, small-diameter materials under test are solid and larger-diameter materials under test can be either solid or hollow. This analysis is restricted to tubular materials under test that satisfies the condition written in Equation (43) as

$$\frac{b}{a} > 4. \quad (43)$$

[0094] Under this condition, the material under test can be treated as flat and the permittivity formula for ϵ_m^e can be used with a correction.

[0095] For a thin dielectric measurement, the reflection coefficients of a dielectric standard are measured, short and open and the material under test ($\Gamma_s, \Gamma_{sc}, \Gamma_{oc}, \Gamma_m$) at the frequencies of interest. Then, calculate the apparent relative permittivity seen by the probe **10**. Calculate the permittivity of the material under test ϵ_m written in Equation **(44)** as

$$\epsilon_m = \frac{\epsilon^*}{1 - [\alpha(\epsilon^* - 1)/t^\beta]} \quad (44)$$

where the probe constants (α and β) were previously determined.

If $\frac{t}{s} \geq 4$ then the dielectric is considered to be infinitely thick and no correction is needed.

[0096] Using the preceding formulas, the method for determining the permittivity of a curved dielectric is summarized in a flowchart of **FIG. 9**. The flowchart can be used as a guide for programming a vector network analyzer (VNA) to collect and process reflection coefficient data.

[0097] The foregoing description of the preferred embodiments of the invention has been presented for purposes of illustration and description only. It is not intended to be exhaustive nor to limit the invention to the precise form disclosed; and obviously many modifications and variations are possible in

light of the above teaching. Such modifications and variations that may be apparent to a person skilled in the art are intended to be included within the scope of this invention as defined by the accompanying claims.

DIELECTRIC MEASUREMENT PROBE FOR CURVED SURFACES

ABSTRACT OF THE DISCLOSURE

A probe is provided for measuring permittivity of a dielectric material. The probe includes side electrodes and a pivotable center electrode with a bulbous tip to contact the material. A mounting harness supports the side electrodes and a feed connector with the center electrode soldered to the connector. The tip includes a contoured surface for measurement and rotation on the material. The bulbous tip can rest perpendicularly or in a pivoted position on the material without a loss of measurement accuracy. A saddle ensures that a measurement of the reflection coefficient is near the bulbous tip. In use, a voltage wave generated by a vector network analyzer is guided between the electrodes toward the tip and into the material. The material reflects this voltage wave back to the analyzer. The ratio of the reflected and forward voltages forms a reflection coefficient as a baseline for measuring permittivity.

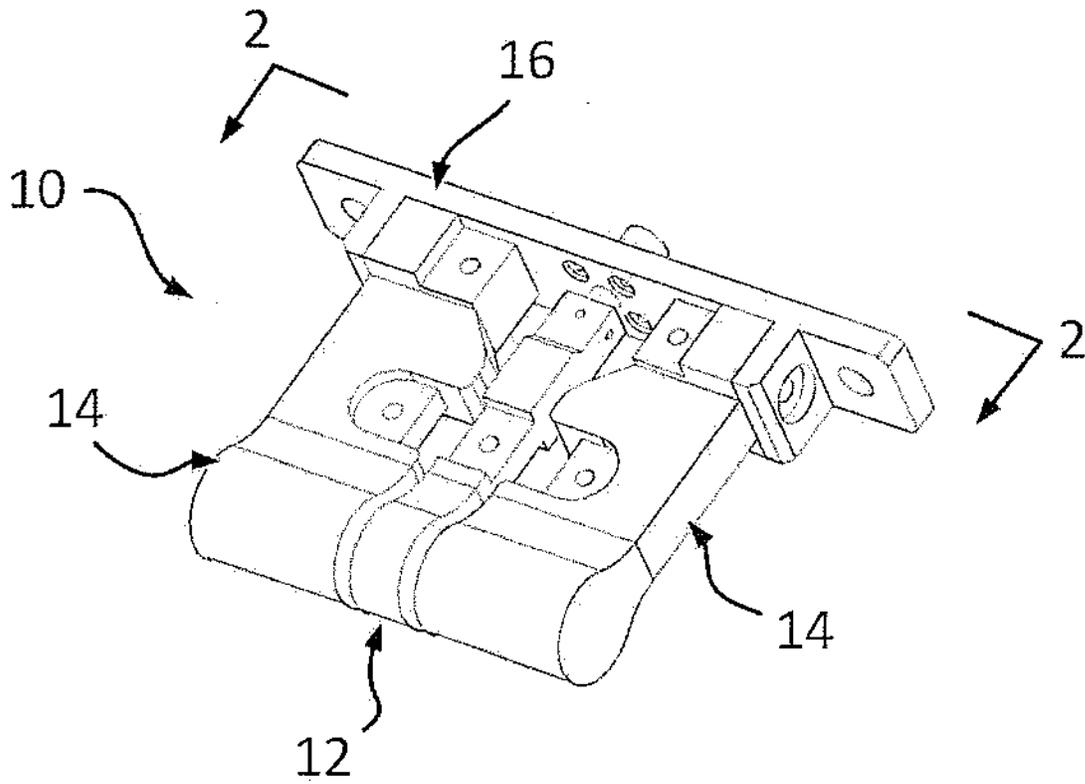


FIG. 1

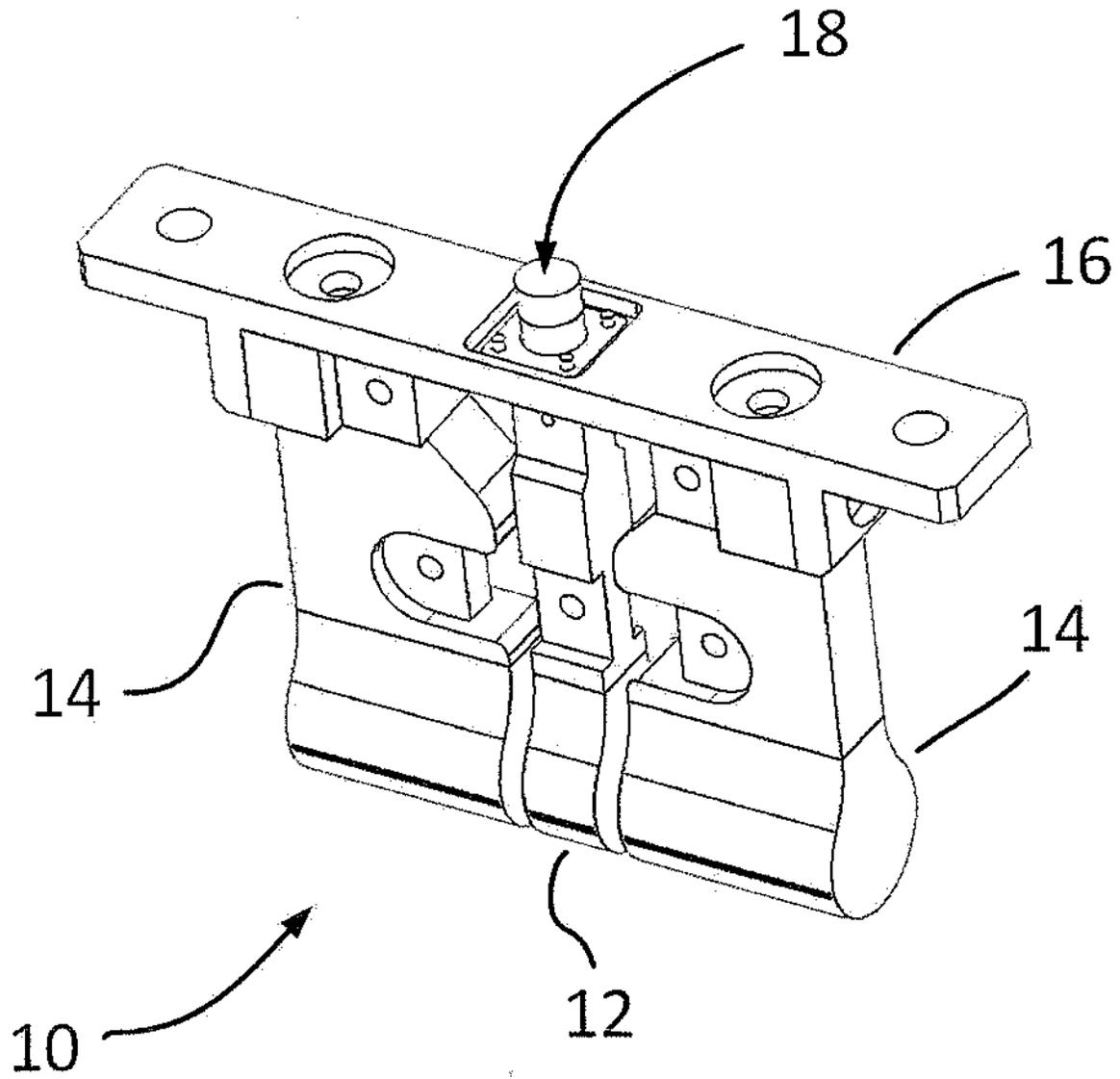


FIG. 2

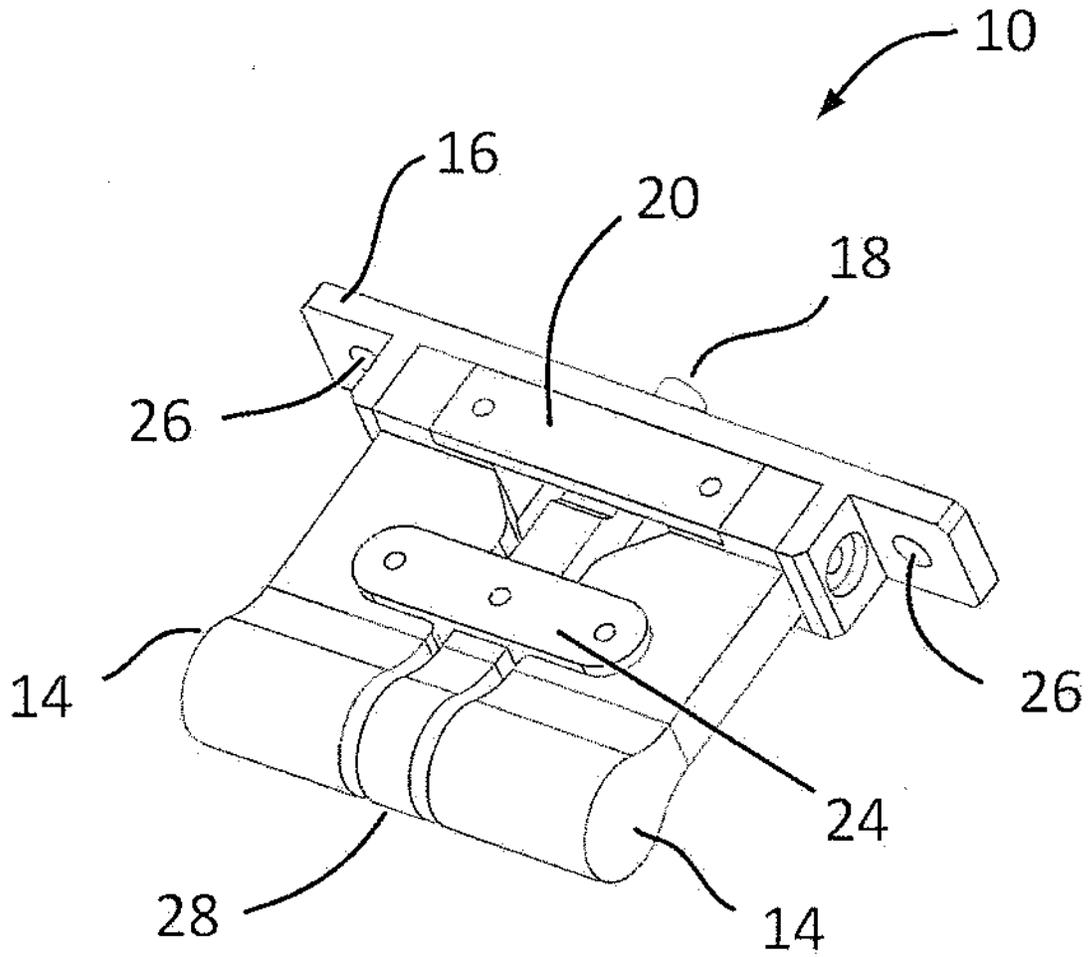


FIG. 3

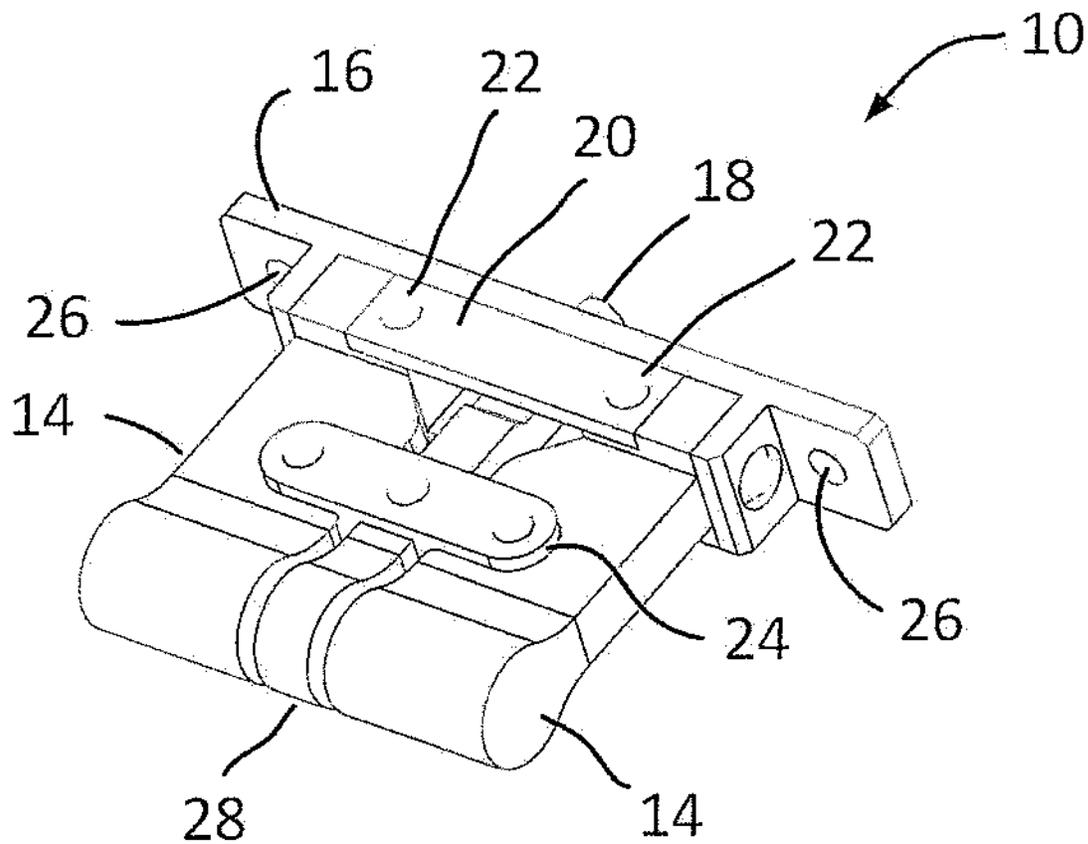


FIG. 4

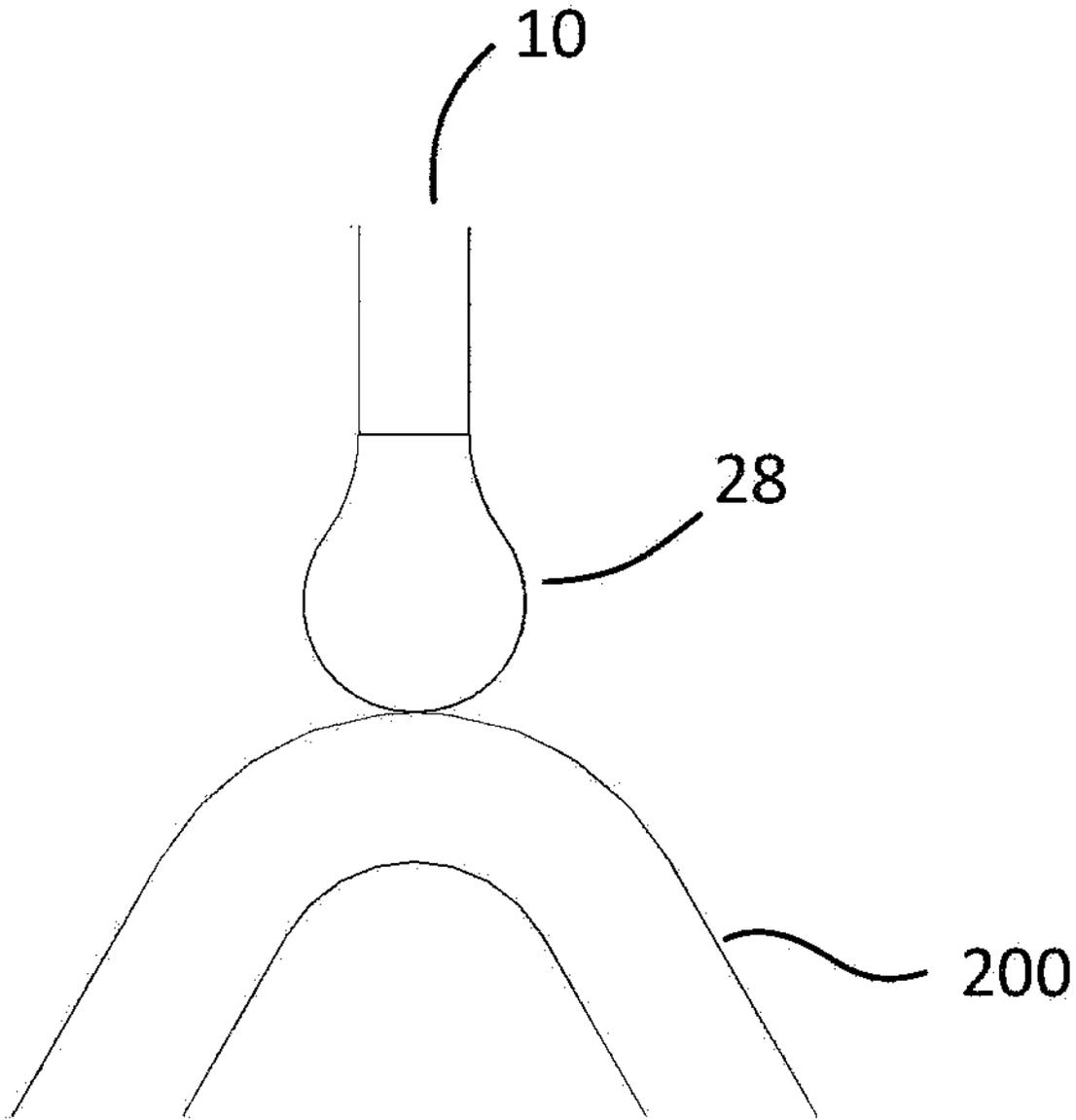


FIG. 5

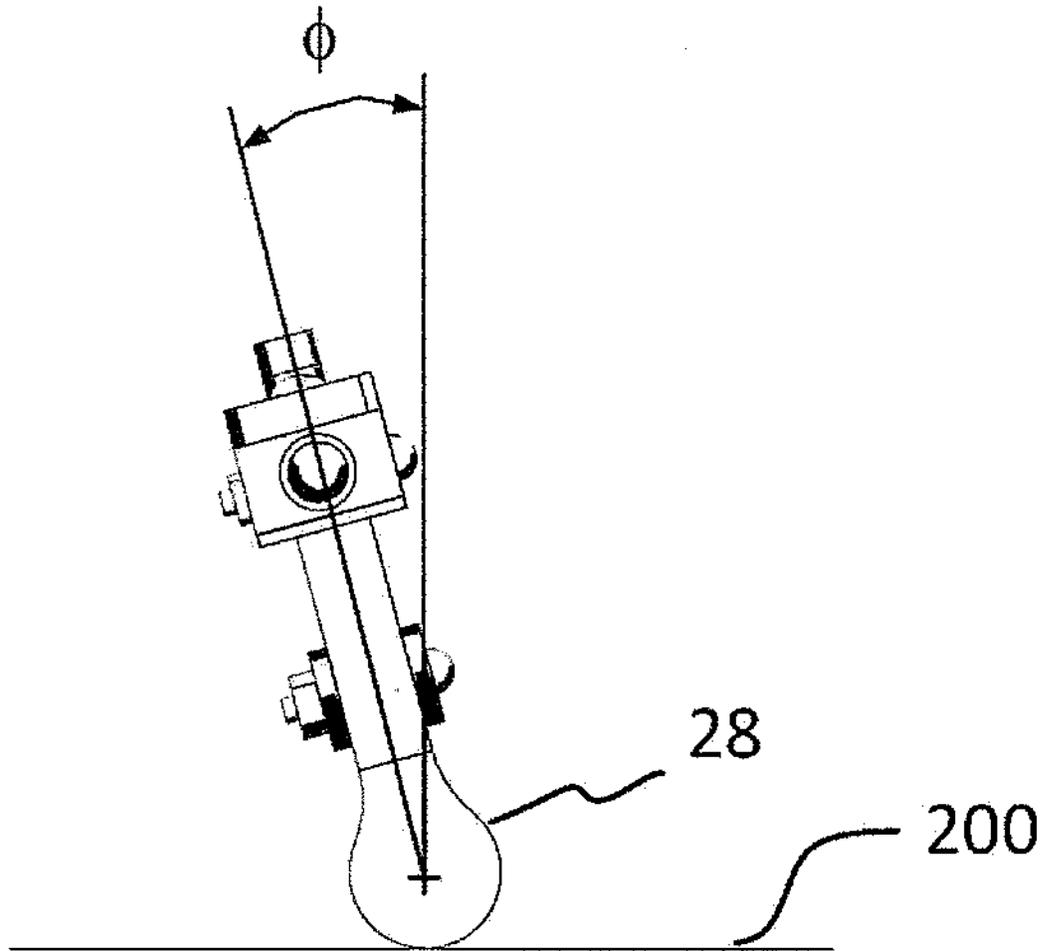


FIG. 6

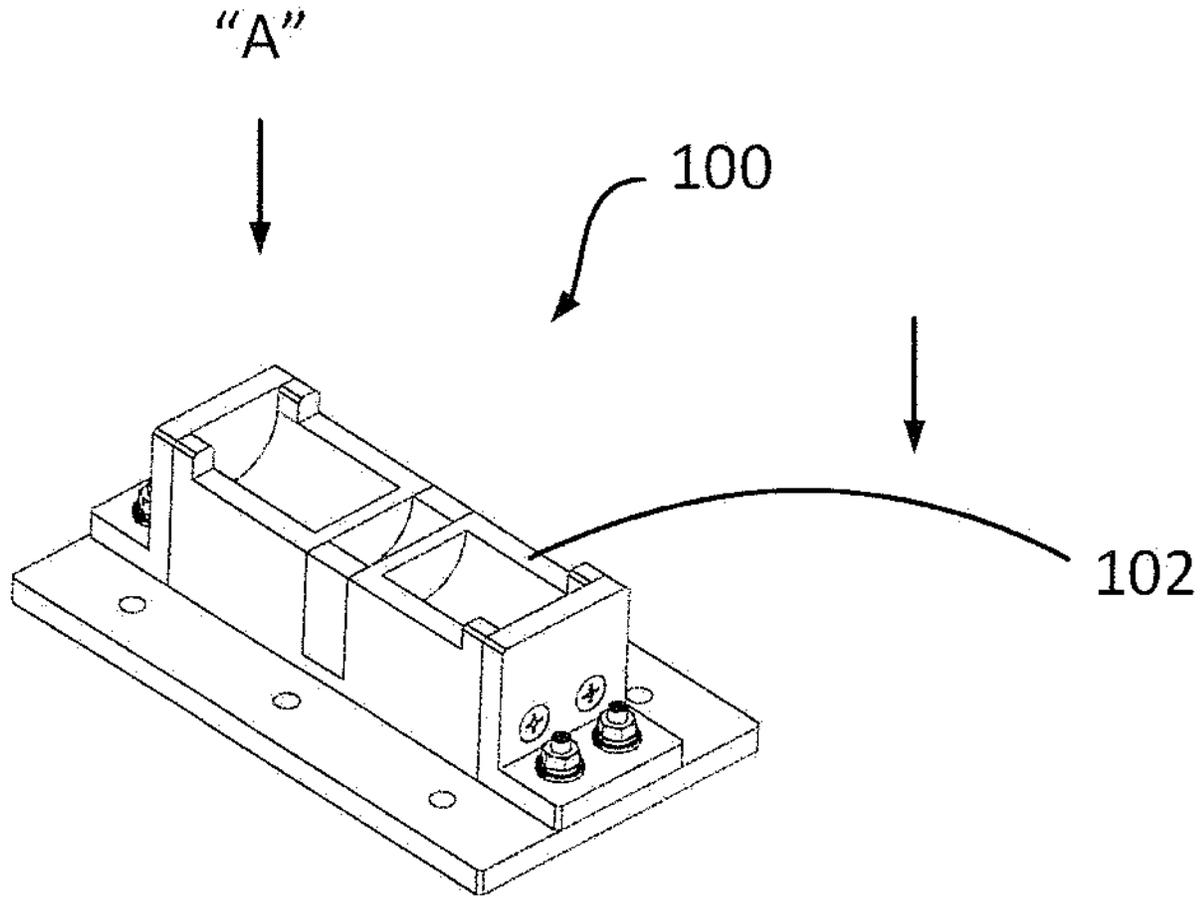


FIG. 7

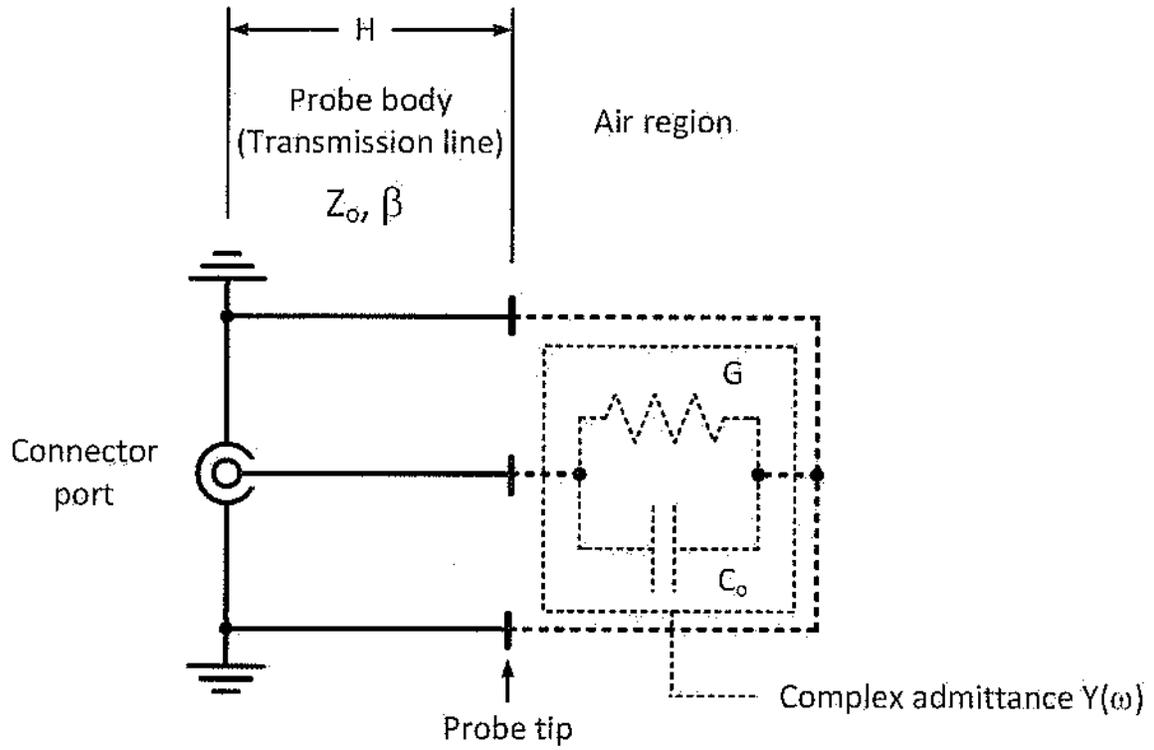


FIG. 8

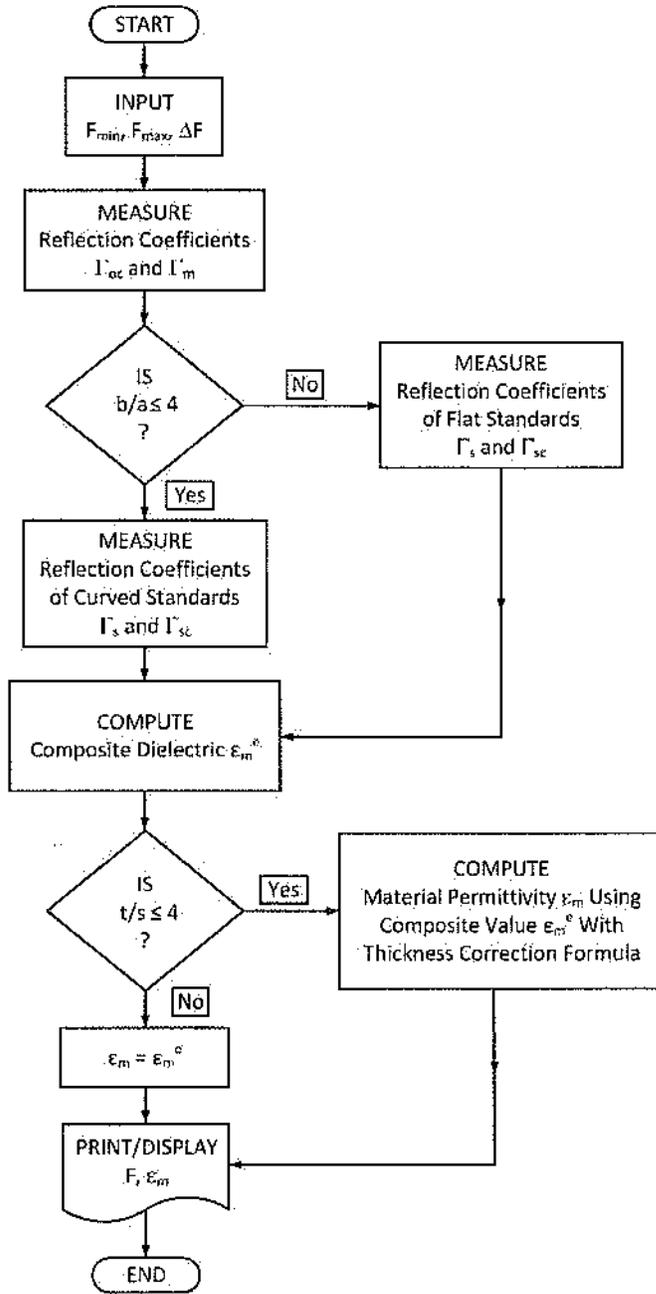


FIG. 9